



**DMP2045UQ** 

### Product Summary

BV <sub>DSS</sub>	RDS(ON) max	Ι <sub>D</sub> T <sub>A</sub> = +25°C
	$45m\Omega @ V_{GS} = -4.5V$	-4.3A
-20V	58mΩ @ V <sub>GS</sub> = -2.5V	-3.8A
	90mΩ @ V <sub>GS</sub> = -1.8V	-3.1A

### Description

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

# **Applications**

- DC-DC Converters
- **Power Management Functions**

### P-CHANNEL ENHANCEMENT MODE MOSFET

### Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP2045UQ is suitable for automotive applications requiring specific change control; it is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.
- https://www.diodes.com/guality/product-definitions/

# **Mechanical Data**

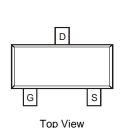
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

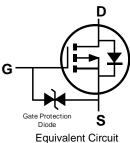




SOT23

Top View





Internal Schematic

## Ordering Information (Note 4)

	Part Number	Compliance	Case	Packaging			
	DMP2045UQ-7	Automotive	SOT23	3,000/Tape & Reel			
	DMP2045UQ-13	Automotive	SOT23	10,000/Tape & Reel			
Notes:							

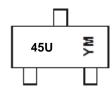
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimonv compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## Marking Information



45U = Product Type Marking Code YM or  $\overline{Y}M$  = Date Code Marking Y or  $\overline{Y}$  = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Kev

Year	2019		2020	2021		2022	2023		2024	2025		2026
Code	G		Н			J	K		L	М		Ν
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-20	V		
Gate-Source Voltage	V <sub>GSS</sub>	±8	V		
Continuous Drain Current (Note 6) $V_{GS} = -4.5V$ Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			I <sub>D</sub>	-4.3 -3.5	A
Maximum Continuous Body Diode Forward Current (	ls	-1.2	A		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-25	A		

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0</sub> JA	154	°C/W	
Total Power Dissipation (Note 6)		PD	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ ext{ heta}JA}$	98	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

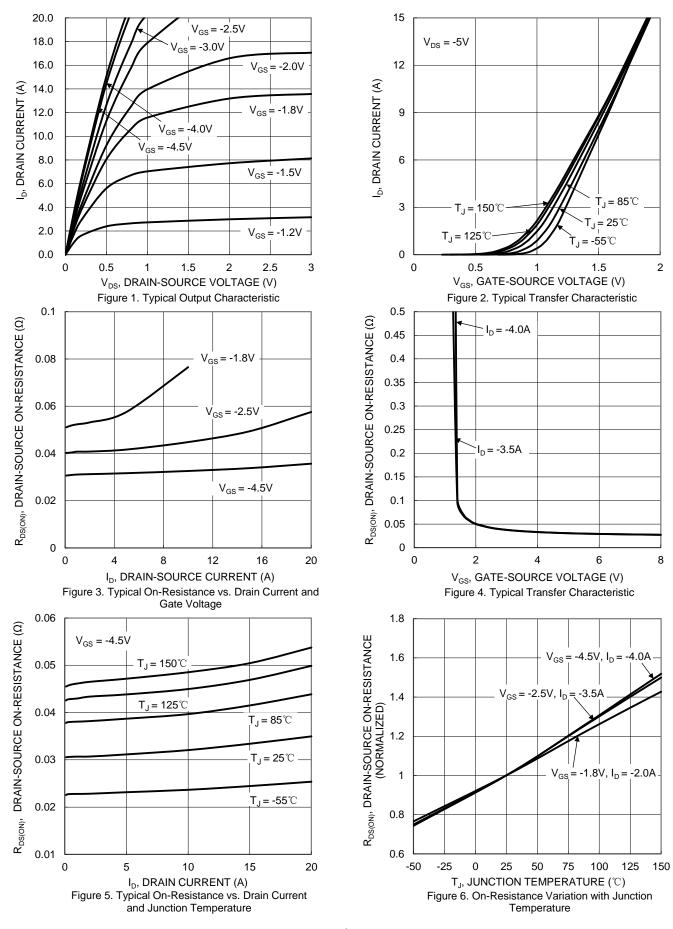
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)					•	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 8.0V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3		-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
		—	32	45		$V_{GS} = -4.5V, I_D = -4.0A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	42	58	mΩ	$V_{GS} = -2.5V, I_D = -3.5A$
		_	54	90		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1.0A
Diode Forward Voltage	V <sub>SD</sub>		-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	_	634	_	pF	
Output Capacitance	Coss	_	81	_	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	66	_	pF	
Gate Resistance	Rg		20		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge	Qg	_	6.8	_	nC	
Gate-Source Charge	Q <sub>gs</sub>		0.7	_	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V I <sub>D</sub> = -4A
Gate-Drain Charge	Q <sub>gd</sub>	_	1.6	_	nC	D = -4A
Turn-On Delay Time	t <sub>D(ON)</sub>		4.2	_	ns	
Turn-On Rise Time	t <sub>R</sub>		3.4		ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>		23		ns	R <sub>L</sub> = 3.3Ω, R <sub>G</sub> = 1Ω
Turn-Off Fall Time	t <sub>F</sub>	—	9.6	_	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	1.8	_	ns	I <sub>F</sub> = -1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	_	9.4	_	nC	I <sub>F</sub> = -1.0A, di/dt = 100A/µs

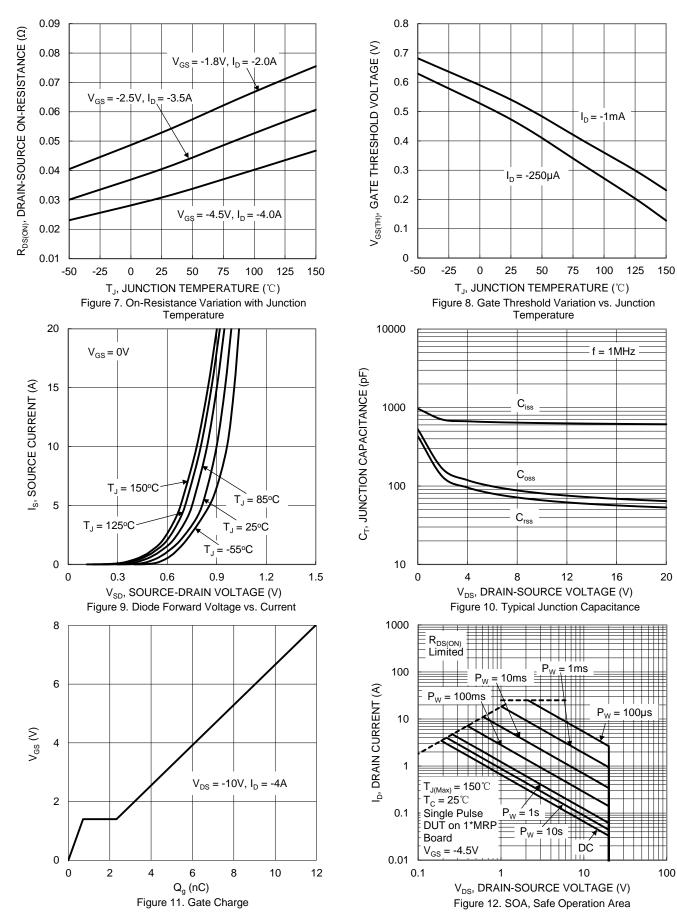
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.



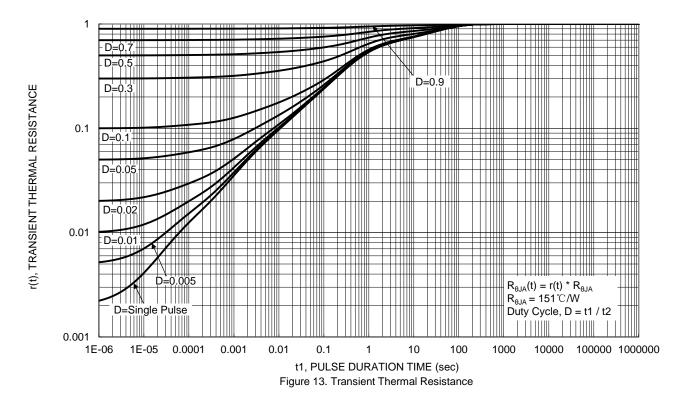






DMP2045UQ Document number: DS41642 Rev. 2 - 2



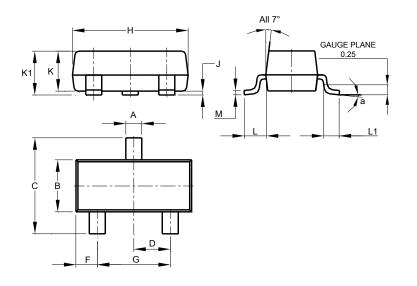




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

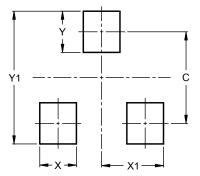


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All	All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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